

ABSTRACT

The invention ~~aims to provide~~ provides a semiconductor device and a method for manufacturing the same that are capable of improving the product performance and operational efficiency of a cross-point ~~FeRAM-FeRAM~~, as well as increasing the area of capacitors included in the cross-point FeRAM. An upper electrode supporting layer forming ~~mask-M1-mask~~ for forming an upper electrode supporting ~~layer-2C-is~~ layer can be made of a hard mask material. By making use of the upper electrode supporting layer forming ~~mask-M1-mask~~ remaining unremoved in forming and processing a lower electrode ~~layer-2A,-layer,~~ prior to forming an upper electrode ~~layer-2D,-layer,~~ a region where a ferroelectric ~~capacitor-C~~ capacitor is formed ~~is~~ can be made larger than an area occupied by an intersection of the upper electrode ~~layer-2D-layer~~ and the lower electrode ~~layer-2A-layer~~.